

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage⁽¹⁾ (T _J = -40 to +125°C, ½ sine wave, 50 to 60Hz, gate open) MAC210-4, MAC210A-4 MAC210-5, MAC210A-5 MAC210-6, MAC210A-6 MAC210-7, MAC210A-7 MAC210-8, MAC210A-8 MAC210-9, MAC210A-9 MAC210-10, MAC210A-10	V _{DRM}	200 300 400 500 600 700 800	Volts
RMS on-state current (full sine wave, 50 to 60Hz, T _C = 70°C)	I _{T(RMS)}	10	Amps
Peak non-repetitive surge current (1 cycle, 60 Hz, T _C = 70°C, preceded and followed by rated current)	I _{TSM}	100	Amps
Circuit fusing considerations (t = 8.3ms)	I ² t	40	A ² s
Peak gate power (T _C = 70°C, pulse width = 10µs)	P _{GM}	20	Watts
Average gate power (T _C = 70°C, t = 8.3ms)	P _{G(AV)}	0.35	Watts
Peak gate current (T _C = 70°C, pulse width = 10µs)	I _{GM}	2.0	Amps
Operating junction and storage temperature range	T _J , T _{stg}	-40 to +125	°C

Note 1: V_{DRM} for all types can be applied on a continuous basis. Blocking voltage shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R _{θJC}	2.2	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ.	Max	Unit
Peak blocking current (Rated V _{DRM} @ T _J = 25°C) (Rated V _{DRM} @ T _J = 125°C)	I _{DRM}	-	-	10 2	µA mA
Peak on-state voltage (either direction) (I _{TM} = 14A peak, pulse width = 1 to 2 ms, duty cycle ≤ 2%)	V _{TM}	-	1.2	1.65	Volts
Gate trigger current (continuous dc) (main terminal voltage = 12V, R _L = 100Ω) MT2(+),G(+) MT2(+),G(-) MT2(-),G(-) MT2(-),G(+) "A" suffix only	I _{GT}	-	12 12 20 35	50 50 50 75	mA

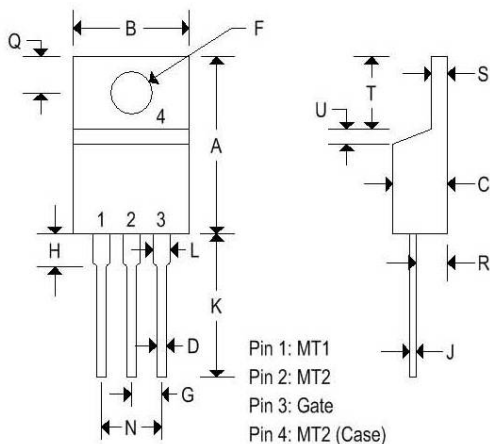
MAC210(A) SERIES

SILICON BIDIRECTIONAL THYRISTORS

Gate trigger voltage (continuous dc) (main terminal voltage = 12V, $R_L = 100\Omega$) MT2(+),G(+) MT2(+),G(-) MT2(-),G(-) MT2(-),G(+) "A" suffix only (main terminal voltage= Rated V_{DRM} , $R_L = 10k\Omega$, $T_J = 125^\circ C$) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" suffix only	V_{GT}	- - - -	0.9 0.9 1.1 1.4	2 2 2 2.5	Volts
Holding current (either direction) (main terminal voltage= 12V, gate open, initiating current = 500mA, $T_C = 25^\circ C$)	I_H	-	6	50	mA
Turn on time (Rated V_{DRM} , $I_{TM} = 14A$, $I_{GT} = 120mA$, rise time = 0.1 μs , pulse width = 2 μs)	t_{gt}	-	1.5	-	μs
Critical rate of rise of commutation voltage ($V_D =$ Rated V_{DRM} , $I_{TM} = 14A$, commutating $di/dt = 5.0A/ms$, gate unenergized, $T_C = 70^\circ C$)	$dv/dt(c)$	-	5	-	V/ μs
Critical rate of rise of off-state voltage ($V_D =$ Rated V_{DRM} , exponential voltage rise, gate open, $T_C = 70^\circ C$)	dv/dt	-	100	-	V/ μs

MECHANICAL CHARACTERISTICS

Case	TO-220AB
Marking	Alpha-numeric
Pin out	See below



	TO-220AB			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.575	0.620	14.600	15.750
B	0.380	0.405	9.650	10.290
C	0.160	0.190	4.060	4.820
D	0.025	0.035	0.640	0.890
F	0.142	0.147	3.610	3.730
G	0.095	0.105	2.410	2.670
H	0.110	0.155	2.790	3.930
J	0.014	0.022	0.360	0.560
K	0.500	0.562	12.700	14.270
L	0.045	0.055	1.140	1.390
N	0.190	0.210	4.830	5.330
Q	0.100	0.120	2.540	3.040
R	0.080	0.110	2.040	2.790
S	0.045	0.055	1.140	1.390
T	0.235	0.255	5.970	6.480
U	-	0.050	-	1.270
V	0.045	-	1.140	-
Z	-	0.080	-	2.030

FIGURE 1 — CURRENT DERATING

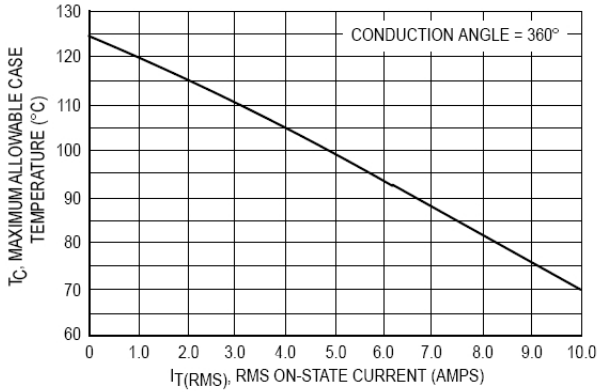


FIGURE 2 — POWER DISSIPATION

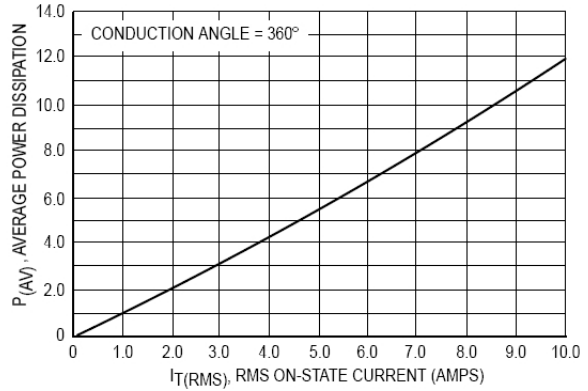


FIGURE 3 — MAXIMUM ON-STATE CHARACTERISTICS

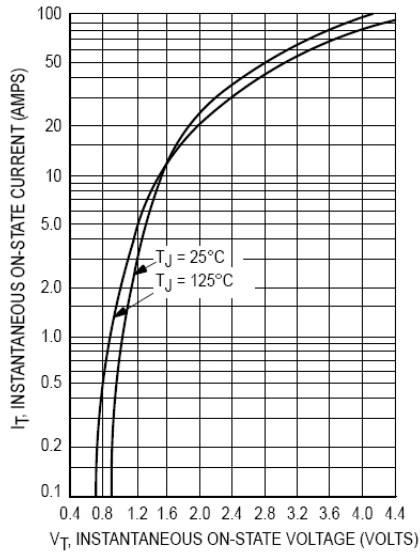


FIGURE 4 — MAXIMUM NON-REPETITIVE SURGE CURRENT

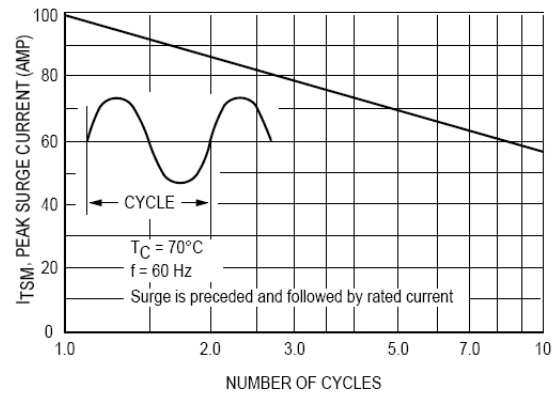


FIGURE 5 — TYPICAL GATE TRIGGER VOLTAGE

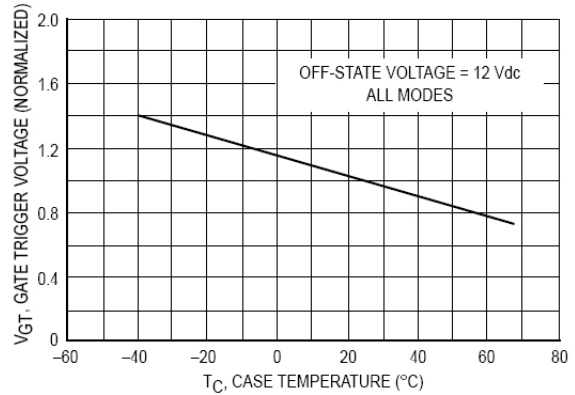


FIGURE 6 — TYPICAL GATE TRIGGER CURRENT

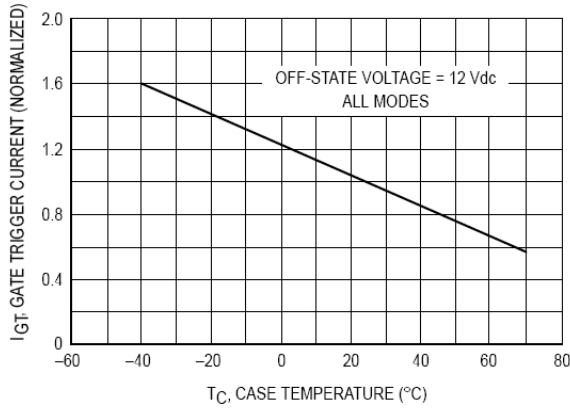


FIGURE 7 — TYPICAL HOLDING CURRENT

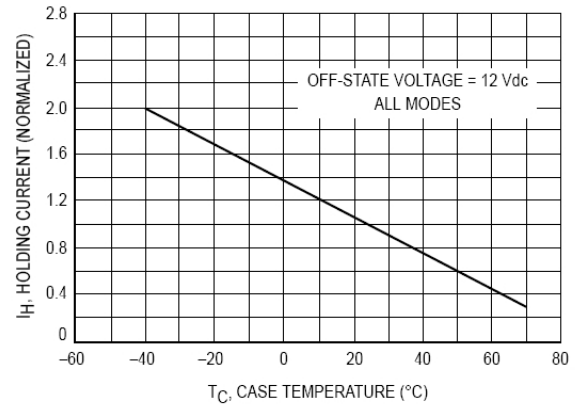


FIGURE 8 — THERMAL RESPONSE

